
IDM



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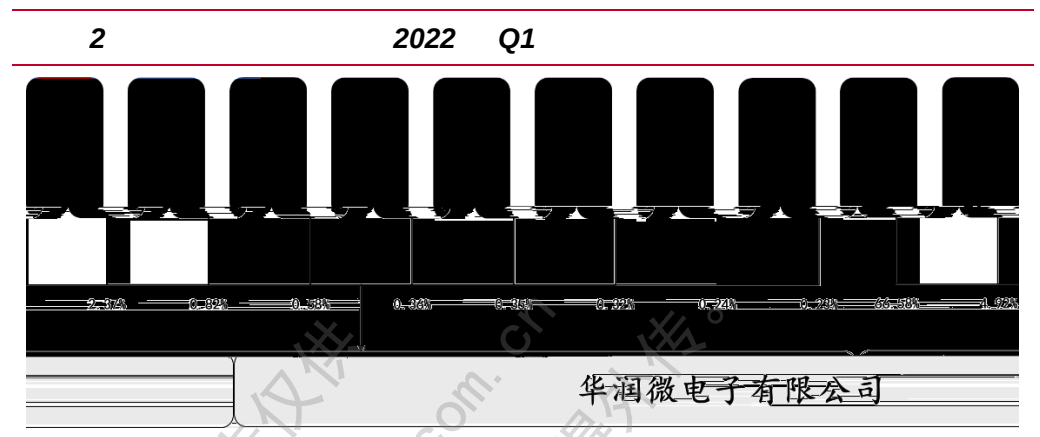
1. IDM

1.1

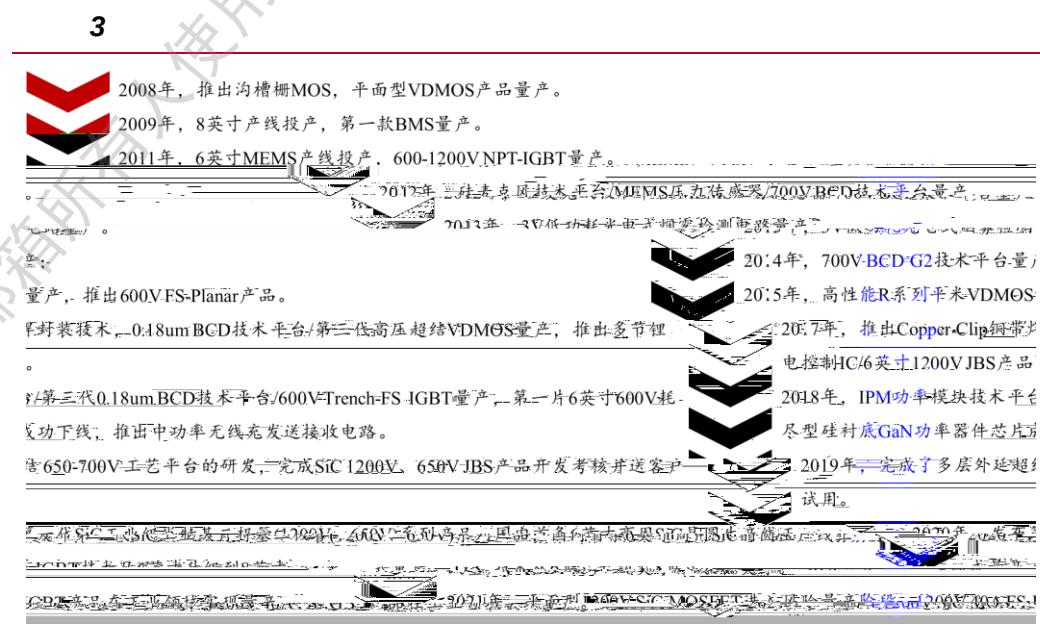
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1.2



1.3



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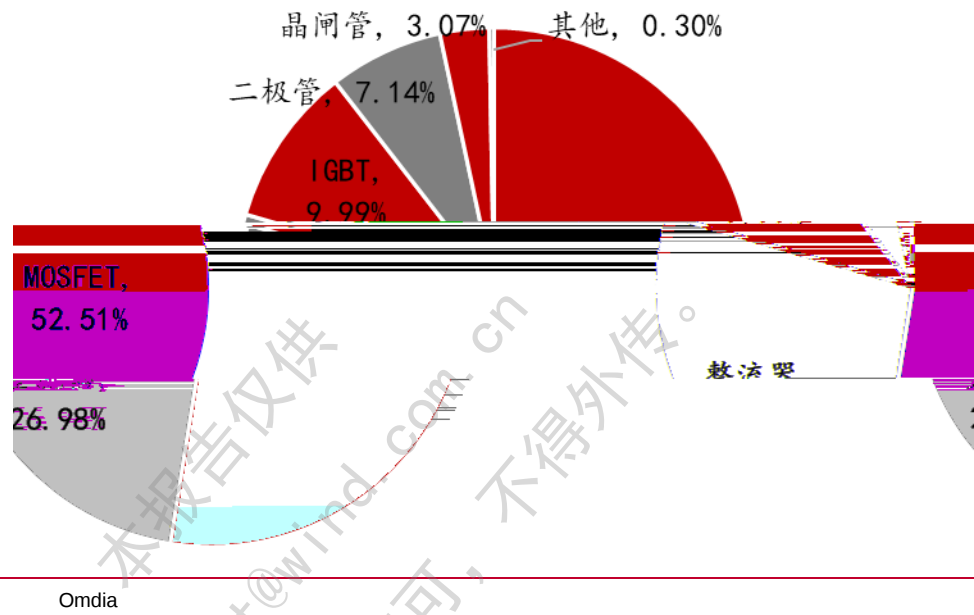
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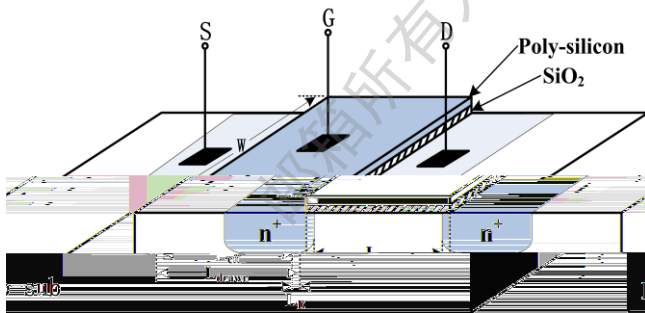
2.

2.1

11 2019

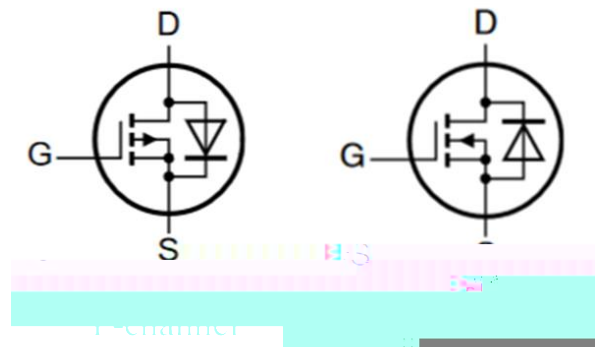


12 MOSFET

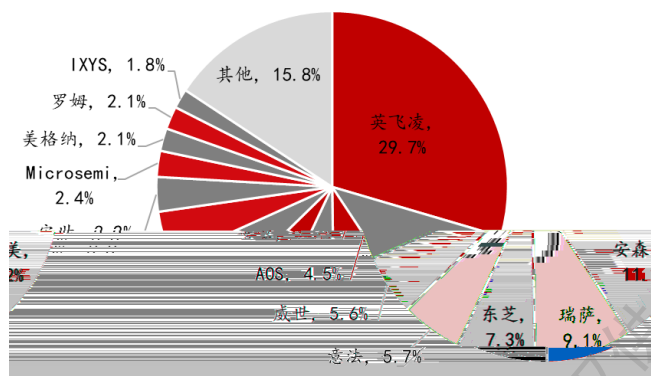


cnblogs

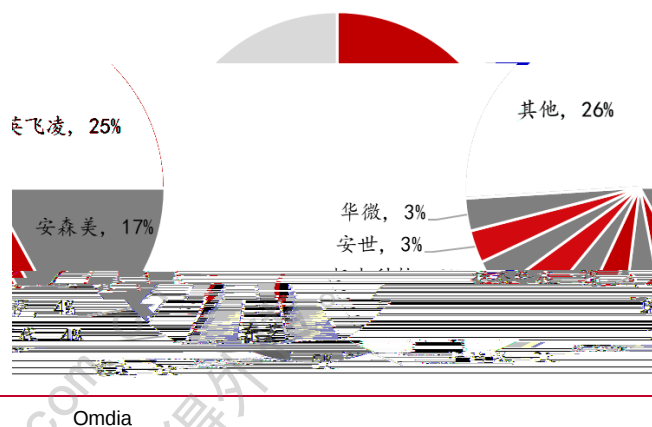
13 P N MOSFET



18 MOSFET 2020

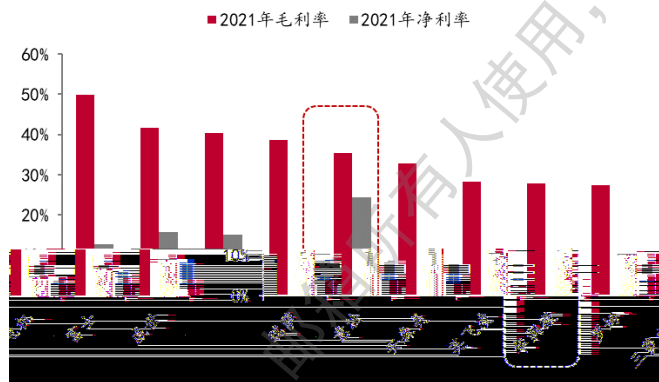


19 MOSFET 2020



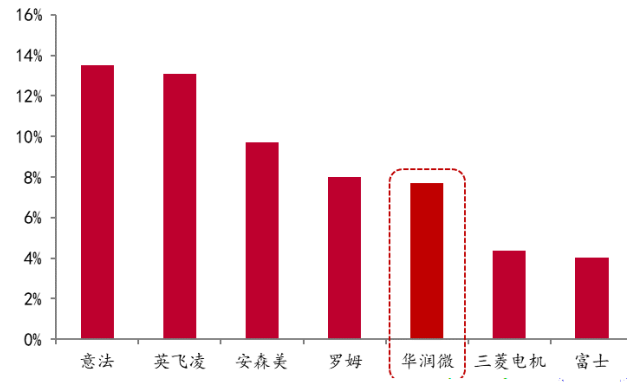
Omdia

20 2021



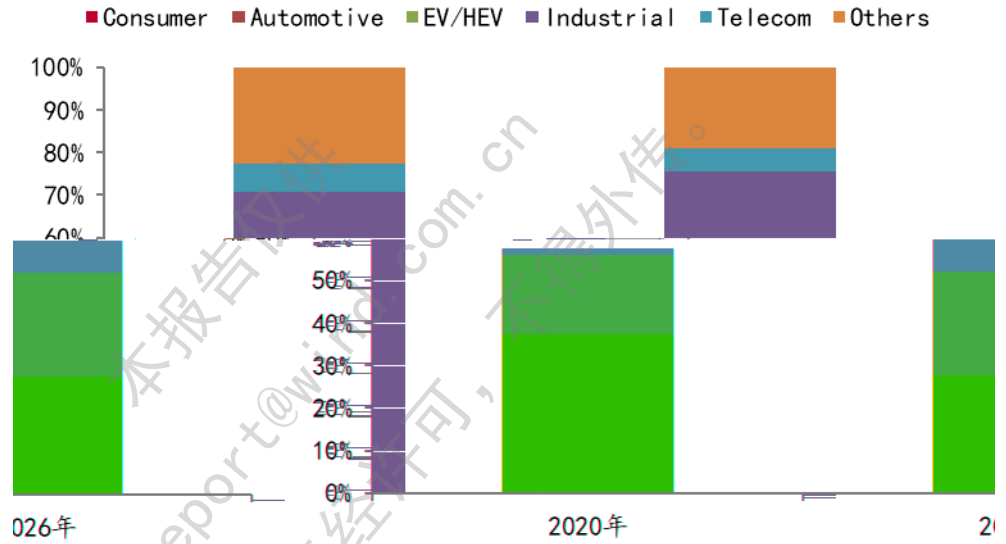
Wind

21 2021



Wind

25 MOSFET 2020-2026



26 2020-2026 MOSFET

Yole

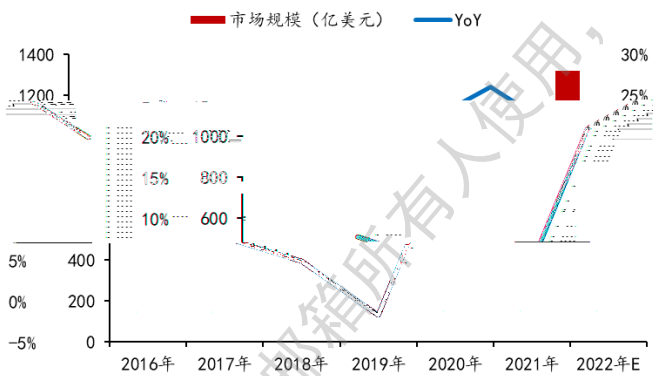
27 Si MOSFET/IGBT/SiC MOSFET

30 2020 IGBT

31 2020-2026 IGBT

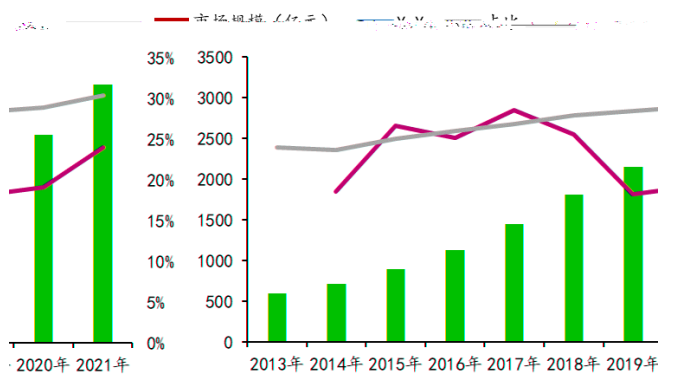
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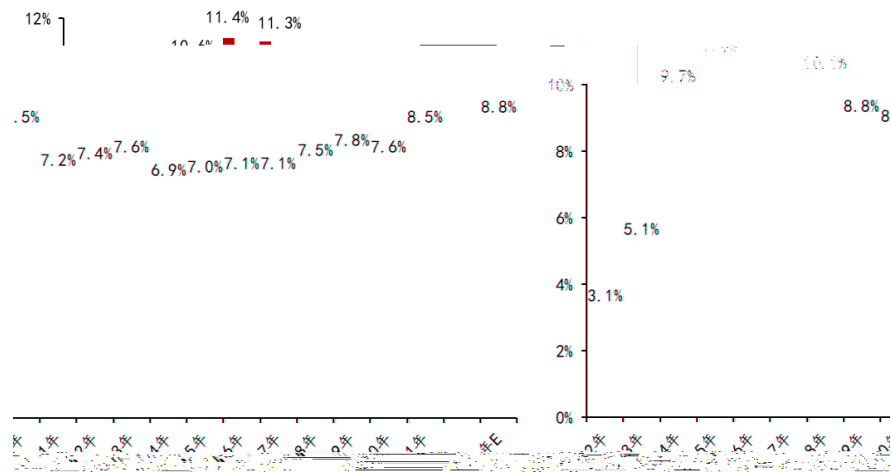


IC Insights

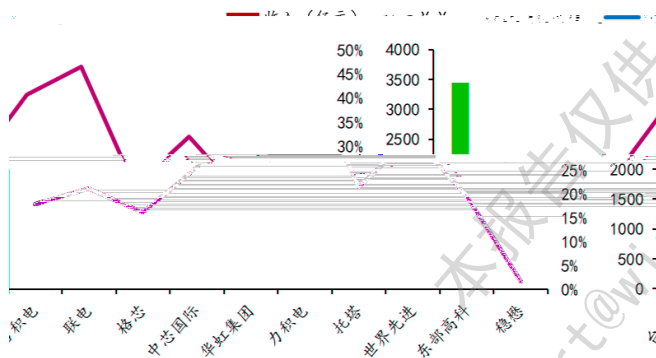
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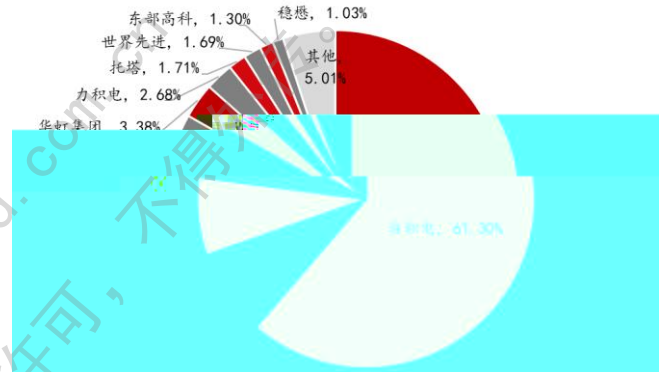
40 2021



ChipInsights

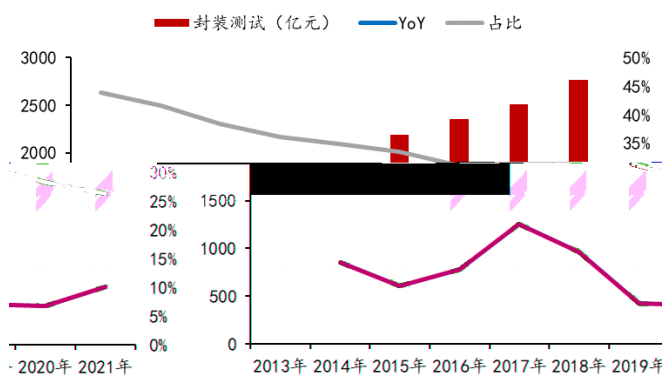
IDM

41 2021

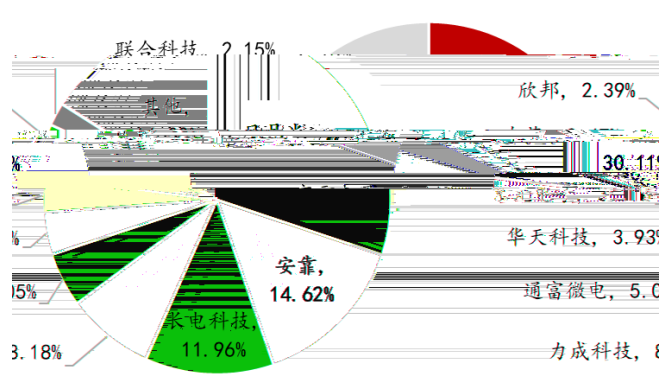


ChipInsights

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ChipInsights

3.

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3.1.

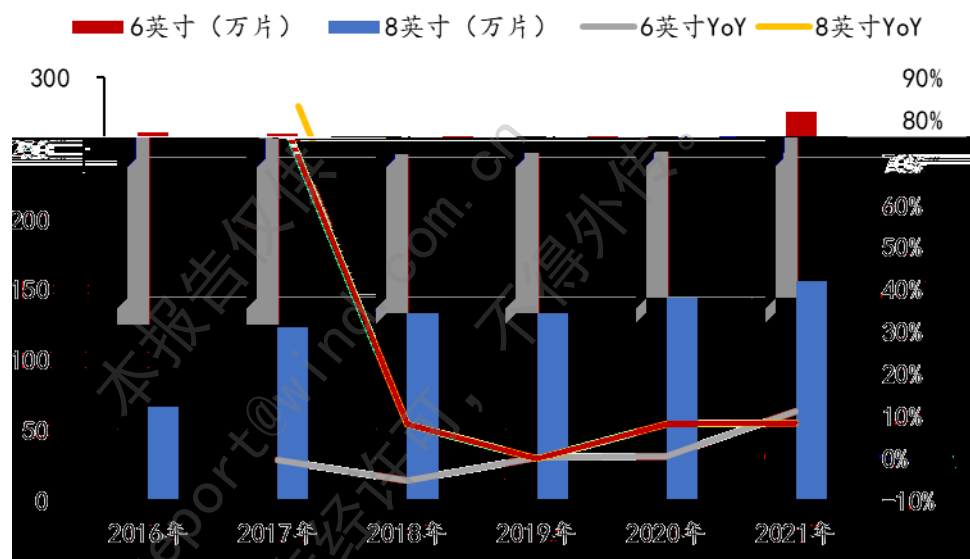
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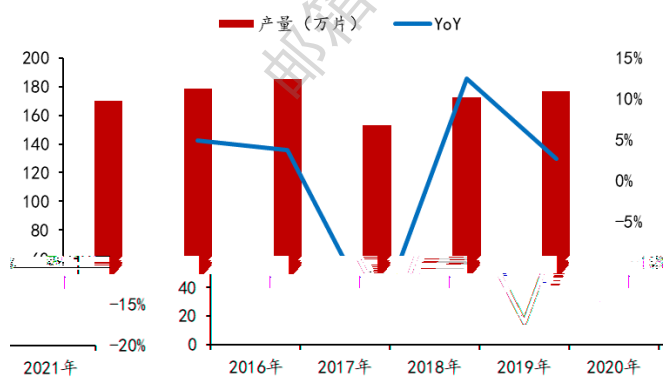
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6

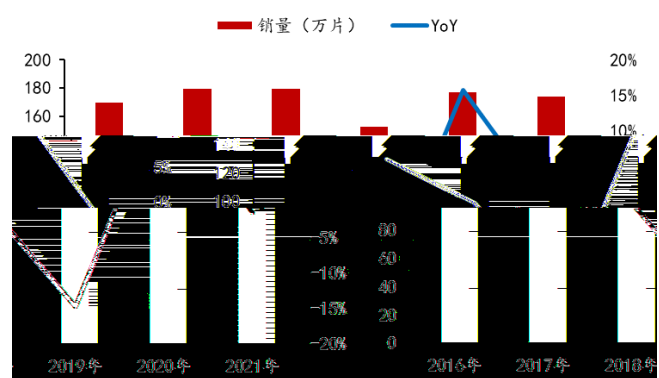
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产品

- 0.18um 及以下 DeepUV 光刻 (5: 1: 4: 1: 1 (JZ))
- 0.13um 及以下 EUV
- 3 "A5" 12.5 光板
- 1:1 Array 掩模
- 掩模光源系统

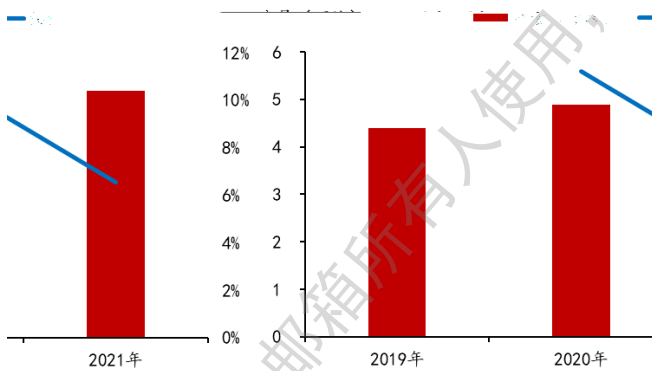
服务

- 提供 Job Deck View
- 制程绝交图 (MIP)
- 制程数据整合
- 制程数据技术是行
- 制程数据专业

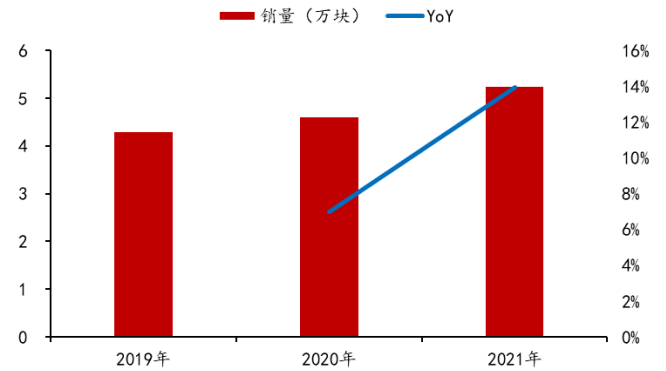
工艺

- 激光及电子束制程工艺
- PSM 工艺
- OPE 工艺
- 干式蚀刻 (Dry Etch)

51



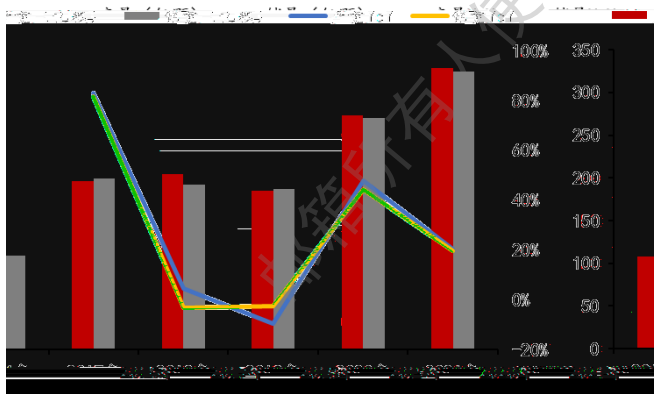
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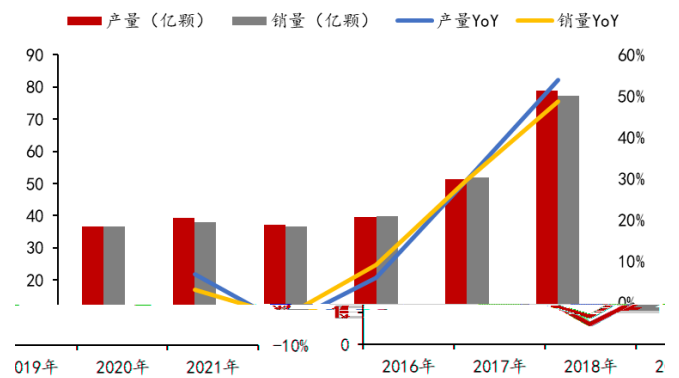
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晶圆测试		封 装			成品测试	
深圳赛美科	无锡安盛	重庆矽磐	深圳赛美科	东莞杰群	深圳赛美科	无锡安盛
						
国内前三大晶圆测试工厂	高可靠性传统IC封装	先进面板封装 成立：2018.11	光耦和硅麦等sensor封装	聚焦功率电子封测业务，Stacks、Modules、MCSP	各类产品成品测试	中高端成品测试 220台套测试设备
销售额：3.5亿	销售额：7.5亿	引进国际先进技术和客户合作一起	开发相应的满足	FETs / IGBTs, Drivers, IPMs, Controllers. 拥有独特的技术优势、知名的管理团队和全球高质量的功率器件	200台套晶圆测试设备	年产能1.2亿颗
220+晶圆测试	IPM module	板封装工艺，提供高能效低成本封装方案，用于功率产品大规模封装，可替代传统QFN、LGA	市场需求的各类sensor		年测试产出30亿颗	高温，常温，低温测试能力，高端工业控制，汽车电子测试
1000激光修调	QFN, LQFP, TSSOP, SSOP, SOT, SOP, ESD package				数字，模拟，混合	
高温测试						
12"：2万片/年						
8*8"：120万片/年						

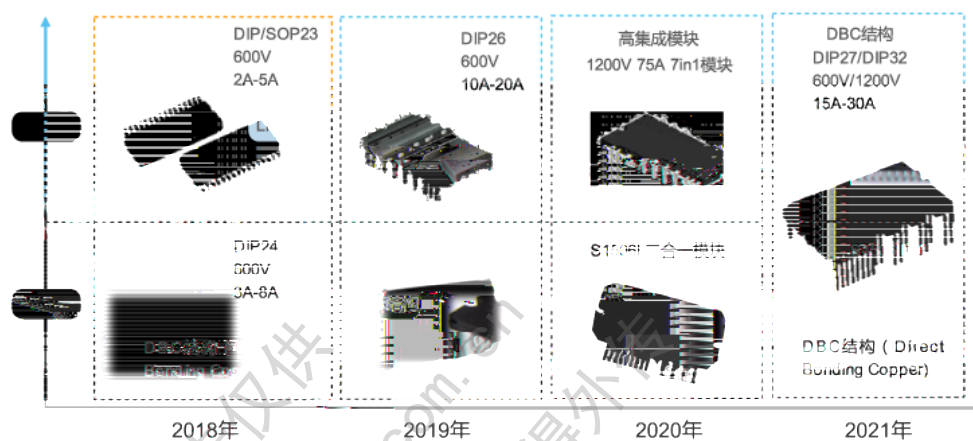
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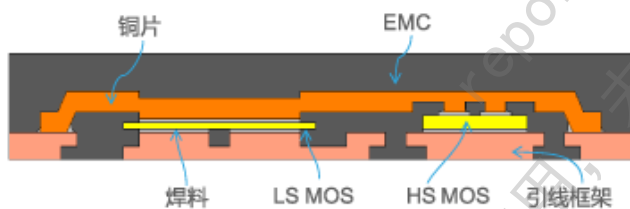
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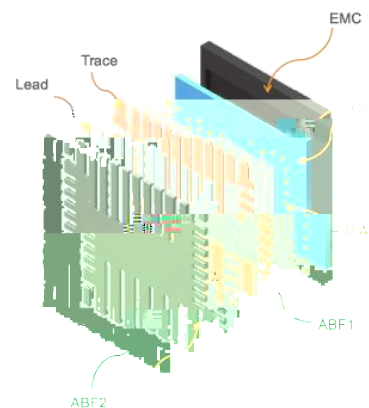
56 IPM



57 Copper Clip



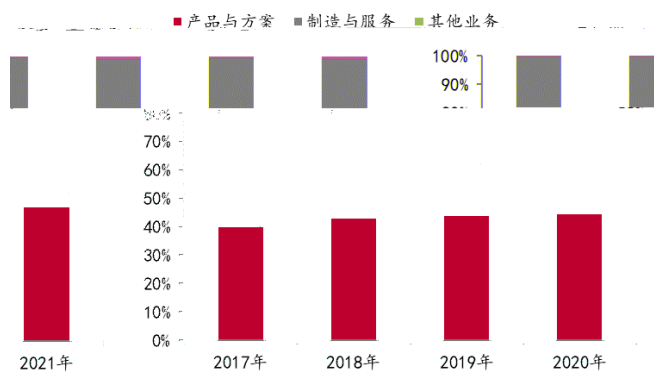
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3.2.

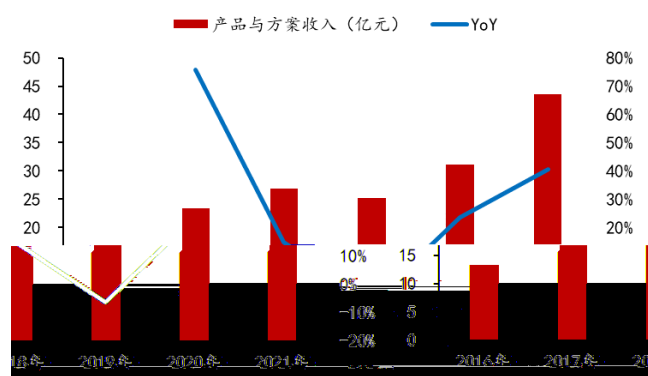
IDM

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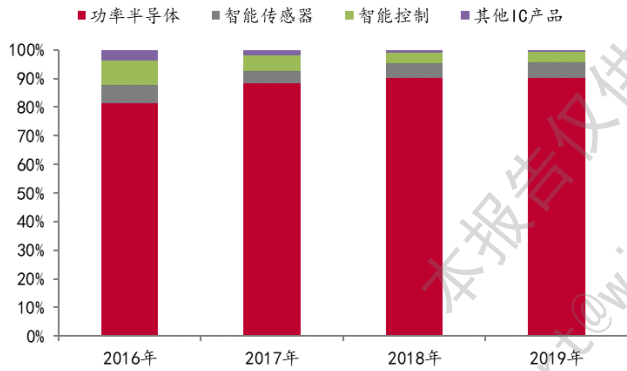


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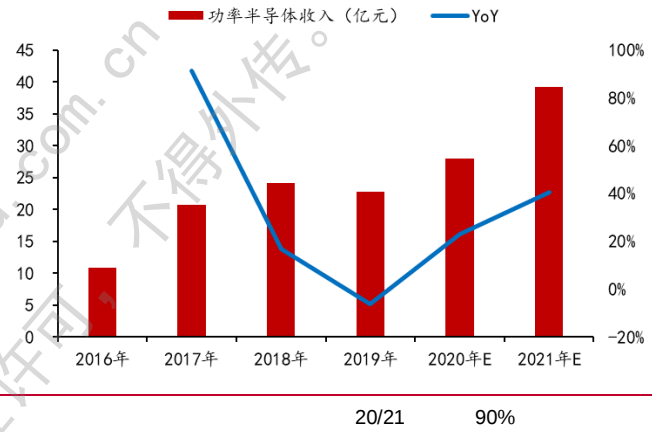
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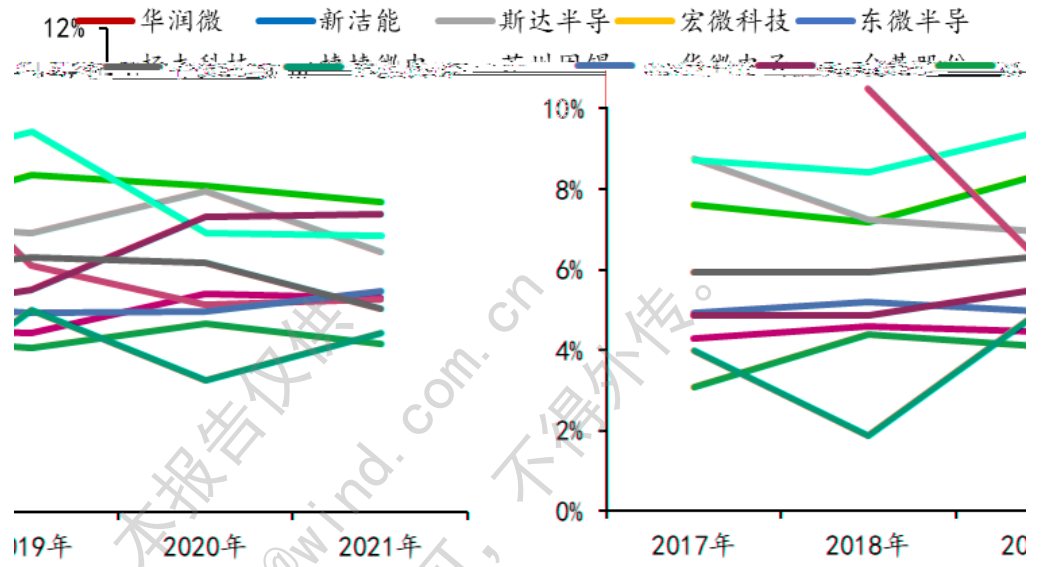


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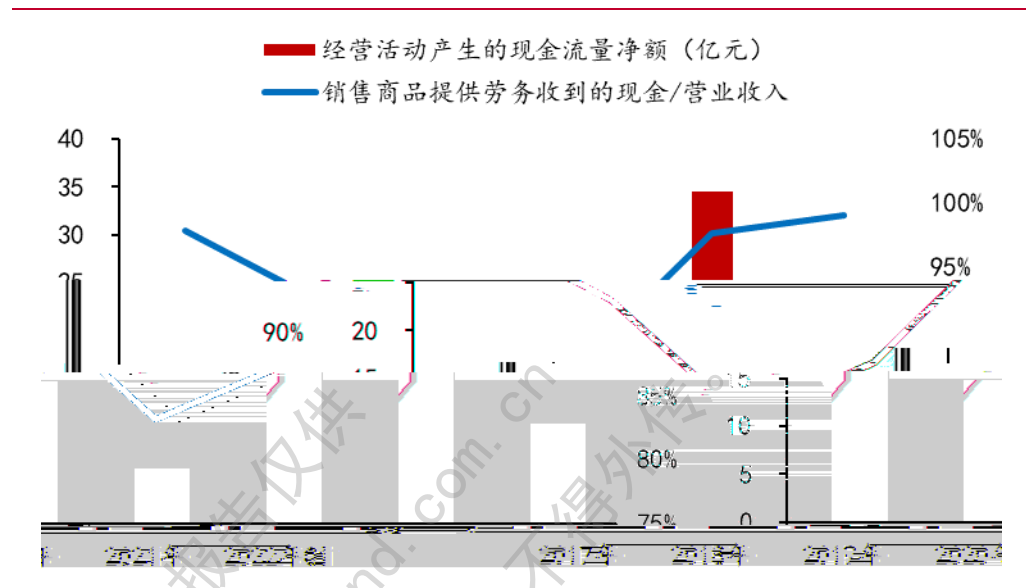
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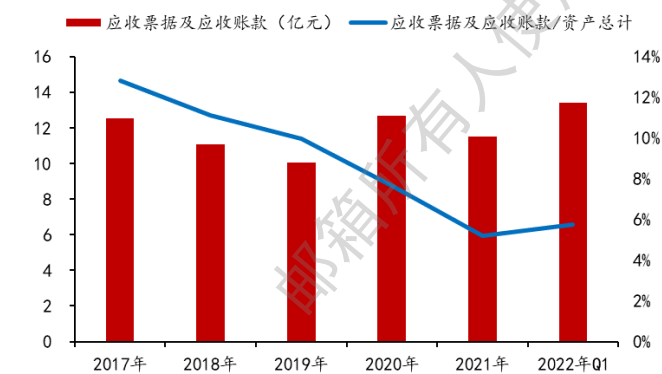


Wind

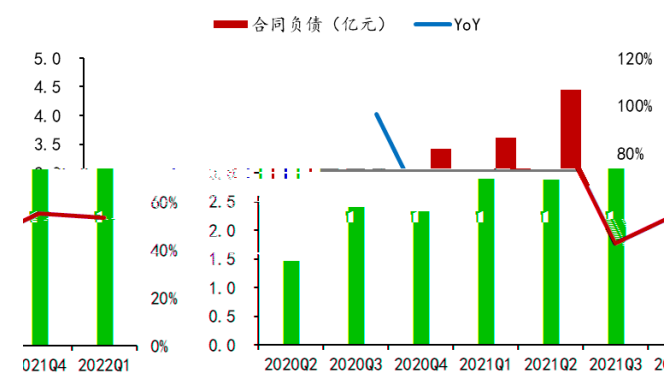
68



72



73



4.

4.1.

Wind

PE

2025-2030

3%

70.95

33

5.



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:	2020A	2021A	2022E	2023E	2024E	2020A	2021A	2022E	2023E	2024E
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